

	Symbol	Min.	Typ.	Max.	Unit	
Gate Threshold Voltage	$V_{(BR)DSS}$	100		1.0	V	
				5.0		
	I_{GSS}			±100	nA	
	$V_{GS(th)}$	1.2	1.9	2.5	V	
			8.3	10.0	m	
			10.8	13.5	m	
		g_{FS}		57	S	
		V_{SD}		0.7	1.0	V
		I_S			89	A
		C_{iss}		1535		pF
	C_{oss}		335		pF	
	C_{rss}		8.2		pF	
	R_g		1.8			
	Q_g		26		nC	
	Q_g		14		nC	
	Q_{gs}		4.3		nC	
	Q_{gd}		6.8		nC	
	$t_{D(on)}$		7.5		ns	
	t_r		15.8		ns	
	$t_{D(off)}$		31		ns	
	t_f		28		ns	
	t_{rr}		43		ns	
	Q_{rr}		35		nC	

Thermal Performance

	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	R_{JA}	42	51	°C/W
Thermal Resistance, Junction-to-Case	R_{JC}	1.1	1.4	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [L = 100 H, $V_{GS} = 10\text{V}$, $V_{DD} = 50\text{V}$] while its value is limited by
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence io - Å a ° t g f g f

Typical Electrical & Thermal Characteristics





TO-252-3L Package Information

